The Challenges of Micro-System Product Development

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Topics

- **MEMS Products**
- **History**
- **Issues of Scale**
- **Fabrication Processes**
- **Reliability & Problems to be solved**
- **New Applications –Approaches Problems to be solved**

MEMS are everywhere!

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Top MEMS Manufacturers in 2006

• http://www.memsinvestorjournal.com/2007/04/ranking_of_t op_.html#more

Vision of Micro-Systems

- **"There's Plenty of Room at the Bottom", 1959, California Institute of Technology**
	- **2 Challenges:**

- **Construct a working electric motor able to fit in a 1/64 inch cube**
- **Print text at a scale that the Encyclopedia Britannica could fit on the head of a pin**

Richard P. Feynman (1918-1988)

William McLellan, 1960

T. Newman, R.F.W. Pease, 1985

The Scale of Things - Nanometers and More

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positioned one at a time with an STM tip Corral diameter 14 nm

Office of Basic Energy Sciences Office of Science, U.S. DOEVersion 05-26-06, pmd

spacing 0.078 nm

Effect of Reduction in Scale

Why does a change is scale matter?

- Entering different physics regimes at a particular scale.
- Physical phenomena scale at different rates which changes their relative importance.

Use a Scaling Parameter to evaluate Scale effects

Geometric Scaling

GEOMETRY SCALING

$$
X_s = S X_0
$$

\n
$$
A_s = X_s Y_s = S^2 X_0 Y_0 = S^2 A_0
$$

\n
$$
V_s = X_s Y_s Z_s = S^3 X_0 Y_0 Z_0 = S^3 V_0 \longrightarrow \bigvee_{d=1}^{d} V_d
$$

hings that depend on olume are going to decrease dramatically

AREA – VOLUME RATIO SCALING

 $A_s/V_s = 1/S (A_o/V_o)$

Things that depend on this ratio will increase in importance

Mechanical Scaling

Mass: cubically reduced

$$
\mathbf{M}_\mathrm{s} = \rho \mathbf{S}^3 \mathbf{V}_\mathrm{o} = \mathbf{S}^3 \mathbf{M}_\mathrm{o}
$$

Stiffness: Linearly reduced

$$
K_{bending} \propto \frac{EI}{L^3} \propto \frac{Ewt^3}{L^3} \propto S
$$

$$
K_{axial} \propto \frac{EA}{L} \propto \frac{Ewt}{L} \propto S
$$

Natural Frequency: increases

$$
f_n = \frac{1}{2\pi} \sqrt{\frac{K}{M}} \propto \sqrt{\frac{K}{M}} \propto \sqrt{\frac{S}{S^3}} \propto \frac{1}{S}
$$

Thermal Scaling

Thermal Mass: *proportional to volume*

 $mc_{p}\Delta T=\rho Vc_{p}\Delta T$

Thermal Conductivity: *Proportional to Area*

 $q = K A \nabla T$ conduction

 $q = hA(T_{w} - T_{\infty})$ convection

 $q = A \sigma T^4$ radiation

Thermal Diffusivity (time constant): *Proportional to Vol/Area*

$$
\tau = \frac{mc_p}{\kappa A} = \left(\frac{\rho c_p}{\kappa}\right)\left(\frac{V}{A}\right) \propto S
$$

Fluidic Scaling

Reynolds Number: A measure of the transition between laminar and turbulent flow

Laminar flow: Re<2000

Turbulent Flow: Re>4000

$$
\text{Re} = \frac{\rho V D}{\mu} \propto S
$$

Micro Domain is dominated by laminar flow.

Scaling of Electrical and Magnetic Fields

Energy Density:
\n
$$
U_{electric} = \frac{1}{2} \varepsilon E^2
$$
 \tE_{breakdown}=3MV/M \Rightarrow U_{electric}=40 J/M³

$$
U_{\text{magnetic}} = \frac{1}{2} \frac{B^2}{\mu} \qquad \qquad B_{\text{sat}} = 1 \text{ T} \implies U_{\text{mag}} = 4 \text{ x } 10^5 \text{ J/M}^3
$$

Magnetic actuation dominates in the Macro world due to the calculations above.

But Magnetics **does not** dominate in the Micro world. Why?

Paschen's Law

Pressure X Separation (atm-M)

F. Paschen, Wied. Ann., 37, 69, 1889

Scaling of Electrical and Magnetic Fields

 $E_{breakdown} = 3x10^8$ V/M for small gap of $\sim 1 \mu m$ or less

$$
\therefore \Rightarrow U_{electric} = 4x10^5 \text{ J/M}^3
$$

which is now comparable to magnetics

However,

- * Magnetics has fabrication issues at the microscale
- •For magnetic field constant $B=B_{sat}$

•Electric Field increases with decreasing gap ($E \propto \frac{1}{S}$) up to the breakdown voltage. $E\varpropto\frac{1}{\tau}$

Physical Phenomena Change The breakdown of the continuum

- **Paschen Effect**
- **M.F.P 0.1 M of air at STP**
- **Material crystal sizes in polycrystalline material** \sim **0.1 µM**
- **Magnetic Domains ~10-25 micron**

A Continuum of Microsystems Fabrication Technologies

Three Dominant MEMS Fabrication Technologies

Surface Micromachining Micromachining

structures formed by deposition and etching of sacrificial and structural thin films.

Silicon Substrate

Bulk Micromachining Micromachining LIGA

Silicon3D structures formed by wet and/or dry etching of silicon substrate.

[100] Wet Etch PatternsSubstrate MembraneGrooveNozzlep++ (B) [111] SiliconSubstrateChannels Holes 54.7o

Dry Etch Patterns Mold

3D structures formed by mold fabrication, followed by injection molding/electroplating

Manufacturing Effect of Reduction in Scale

- Size \int Relative Manufacturing Precision
	- **Dimensional Tolerance/Nominal Dimension**
		- **Micro Scale (1-100m) 0.1% 1%**
		- **Macro Scale (1cm 1m) 0.001%**

Manufacturing Processes Impose constraints on Design

• **Bulk Micromaching Example:** – **Aspect ratio of etches**

• **Surface Micromachining Example**

A Variety of Micro Mechanisms are required for Microdevice Applications

Reliability Concerns Increase With Complexity

Class I

• No Moving Parts *e.g., Pressure Sensors*

Class II

• Moving Parts *e.g., Accelerometers*

Class III

- Moving Parts
- Impacting Surfaces *e.g., Tilting Mirrors*

Class IV

- Moving Parts
- Impacting Surfaces
- Rubbing Surfaces *e.g., Gears*

Understand the science of reliability

Reliability Testing

Sandia High-volume Micromachine Measurement of Reliability

Sandia
National Laboratories

MEM Performance Measurement Issues

- **These are small devices (microns)**
- **Structures may move very fast (>1 kHz, >100000 rpm)**
- **Small displacements can occur (angstroms microns)**
- **Displacements can be in plane or out of plane**
- **High voltages may be required (many 10s of volts)**
- **Complex control signals may be necessary**
- **Direct electrical measurements are not typical**

Applications

MEMS Electrical Contacts

Actuators 73 (1999) 138-143

- **Contact Resistance is a function of Contact Force**
	- **An issue at Microscale**
- **Materials issues**
	- **Contact Stiction**
	- **Contact Resistance change with age and repeated actuation**

Fig. 4. $R_c - F_c$ characteristics of closing AuNi5 contacts: unstable contact at very low force, transition to lower resistance and the domain of stable contact with the measured resistance force characteristic compared to theoretical relationship according to Holm's model, from Ref. [6].

Optical Bench Example

Laser, 3 Fresnel lenses, beam splitter, 45 degree mirror

Dr. Wu, U. of California, Berkley

Retinal Implant

Neural Probes

Applications

MEMS Variable Emittance Louvers

2592 SUMMiT V™ die with Buried Interconnects

Experimental satellites monitor space weather

4"x4" Johns Hopkins/APL Experimental Thermal **Regulator**

3 NASA/Goodard ST5 Microsats Launched 3/22/06

Applications

IBM Millipede Storage System

- **High density data storage possible(Tb/in2)**
- **4x Magnetic Media**
- **AFM tip writes and reads data**
- **Bit set by melting depression into polymer medium**

SiTime Resonators

SiTime's revolutionary MEMS First™ technology allows ultra stable mechanical resonators to be integrated into standard silicon chips with performance as good as or better than traditional quartz-based systems.

SiRes™ mechanical resonator vibrating.

Single crystal Si encapsulation layer allows CMOS integration

PRISM Center can greatly Impact Microsystem Development

- **Improve understanding MEMS reliability**
- **Provide the capability for analysis based design versus empirical or design of experiments approach**
- **Provide the ability to include uncertainty of fabrication process and materials in MEMS designs**
- **Increased understanding of the physics of phenomena.**

